Central™
Semiconductor Corp.

PROCESS CPD98V

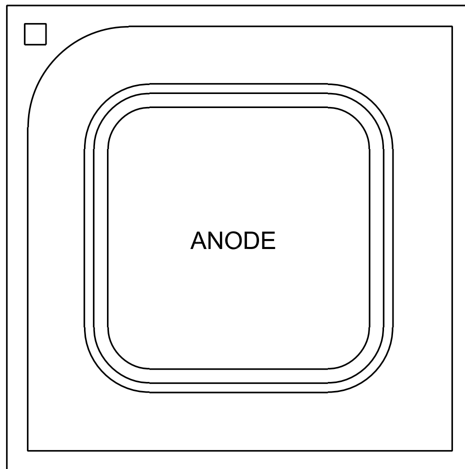
Schottky Diode

Silicon High Current Schottky Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	5.4 x 5.4 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 4 INCH WAFER
93,826

PRINCIPAL DEVICE TYPES
CMUSH2-4 Series

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

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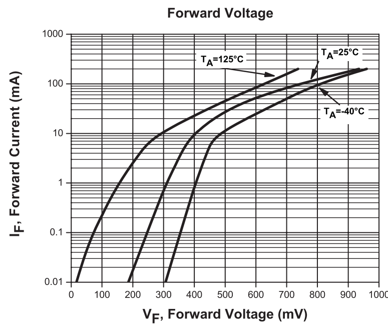
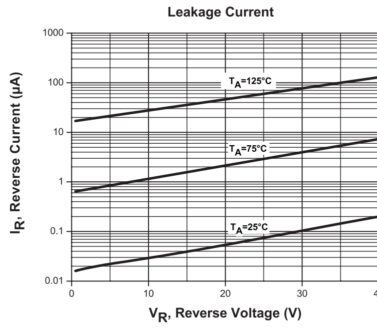
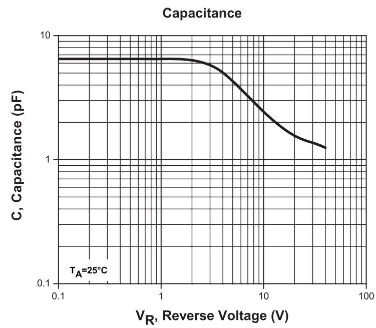
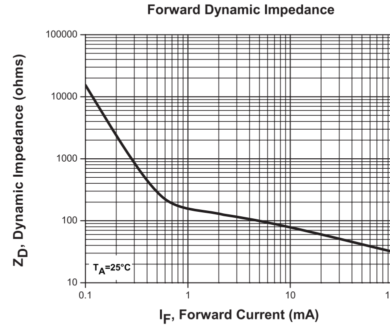
PROCESS CPD98V

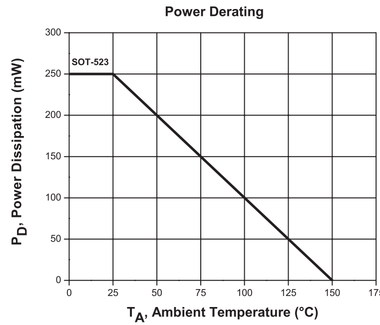
Typical Electrical Characteristics











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